TOSHIBA Field Effect Transistor Silicon P Channel MOS Type ($L^2-\pi$ -MOSV)

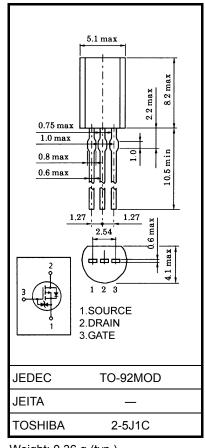
2SJ507

Chopper Regulator, DC–DC Converter and Motor Drive Applications

- 4-V gate drive
- Low drain-source ON resistance $: R_{DS}(ON) = 0.5 \Omega$ (typ.)
- High forward transfer admittance $|Y_{fs}| = 1.0 \text{ S (typ.)}$
- Low leakage current $: IDSS = -100 \ \mu A \ (max) \ (VDS = -60 \ V)$
- Enhancement mode : $V_{th} = -0.8 \sim -2.0 V (V_{DS} = -10 V, I_D = -1 mA)$

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-source voltage		V _{DSS}	-60	V	
Drain-gate voltage (R _{GS} = 20 kΩ)		V _{DGR}	-60	V	
Gate-source voltage	_	V _{GSS}	±20	V	
Drain current	DC (Note 1)	I _D	-1	А	
	Pulse (Note 1)	I _{DP}	-3	А	
Drain power dissipation	ı	PD	0.9	W	
Single pulse avalanche energy (Note 2)		E _{AS}	249.6	mJ	
Avalanche current		I _{AR}	-1	А	
Repetitive avalanche e	nergy (Note 3)	E _{AR}	0.09	mJ	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	



Weight: 0.36 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient	R _{th (ch−a)}	138	°C / W

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: V_{DD} = -25 V, T_{ch} = 25°C (initial), L = 339 mH, R_G = 25 Ω , I_{AR} = -1 A

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Please handle with caution.

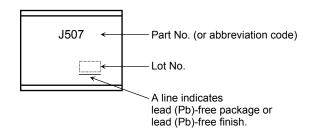
Electrical Characteristics (Ta = 25°C)

Charao	cteristics	Symbol	Test Condition	Min	Тур.	Max	Unit	
Gate leakage cu	ırrent	I _{GSS}	V _{GS} = ±16 V, V _{DS} = 0 V		_	±10	μA	
Drain cut-off cu	rrent	I _{DSS}	V_{DS} = -60 V, V_{GS} = 0 V	_	_	-100	μA	
Drain−source br voltage	eakdown	V (BR) DSS	I _D = -10 mA, V _{GS} = 0 V	-60	_	_	V	
Gate threshold v	/oltage	V _{th}	$V_{DS} = -10 \text{ V}, \text{ I}_{D} = -1 \text{ mA}$	-0.8		-2.0	V	
Drain-source ON resistance		Pro (ou)	V _{GS} = -4 V, I _D = -0.5 A	_	0.72	1.0	Ω	
		R _{DS (ON)}	V _{GS} = -10 V, I _D = -0.5 A	_	0.5	0.7		
Forward transfe	r admittance	Y _{fs}	V _{DS} = -10 V, I _D = -0.5 A	0.5	1.0		S	
Input capacitance	xe	C _{iss}		_	170	_		
Reverse transfer capacitance		C _{rss}	V _{DS} = -10 V, V _{GS} = 0 V, f = 1 MHz	_	25	_	pF	
Output capacitance		Coss			72	_		
Switching time	Rise time	tr	$V_{GS} \xrightarrow{0V} I_{D} = -0.5A$ $V_{GS} \xrightarrow{10V} V_{OUT}$ $R_{L} = 60\Omega$ $V_{DD} = -30V$ $Duty \leq 1\%, t_{W} = 10\mu s$	_	20	_		
	Turn-on time	t _{on}		_	35	_		
	Fall time	t _f		_	30	_	- ns	
	Turn-off time	t _{off}		_	135	_		
Total gate charge (Gate-source plus gate-drain)		Qg	V _{DD} ≈ −48 V, V _{GS} = −10 V,	_	5.6		nC	
Gate-source charge		Q _{gs}	$I_{\rm D} = -1 {\rm A}$	_	3.9	—		
Gate-drain ("miller") charge		Q _{gd}		_	1.7	_		

Source–Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	_	_	_	-1	А
Pulse drain reverse current (Note 1)	I _{DRP}	_			-3	А
Forward voltage (diode)	V _{DSF}	I _{DR} = -1 A, V _{GS} = 0 V	-	-	1.5	V
Reverse recovery time	t _{rr}	I _{DR} = −1 A, V _{GS} = 0 V dI _{DR} / dt = 50 A / μs		58		ns
Reverse recovery charge	Q _{rr}			72.5		nC

Marking



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20070701-EN

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